Notice of References Cited Application/Control No. | Applicant(s)/Patent Under Reexamination | TSUBATA ET AL. | Examiner | Art Unit | Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	Α	US-			
	В	US-			
	С	US-			
	ם	US-			
	Е	US-			
	F	US-			
	G	US-			
	Н	US-			
	1	US-			
	J	US-			
	к	US-			
	L	US-			
	М	US-		·	

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	EP 1154036 A1	11-2001	European Patent	ROBERTSON et al.	
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	Р					
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	Т					

NON-PATENT DOCUMENTS

		NON-I ATENT BOOOMENTO
*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Cicala et al, Plasma deposition of amorphous silicon alloys from fluorinated gases, Pure & Appl. Chem., Vol. 68, No. 5, 1996, pp. 1143-1149
	٧	Ohta et al., Ultrathin fluorinated silicon nitride gate dielectric films formed by remote plasma enhanced chemical vapor deposition employing NH3 and SiF4, Journal of Applied Physics, Vol. 90, No. 4, 2001, pp. 1955-1961
	w	
	x	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)

Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.